

Serial No. 10/034,379

OKI:291

Amendment dated May 10, 2004

Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (currently amended): A method for selectively oxidizing a silicon wafer, said method comprising:

covering each of whole areas of both surfaces of a silicon wafer with an oxidation inhibitor film with interposition of a pad oxide film;

B patterning said pad oxide film and an oxidation inhibitor film on said pad oxide film on one surface of said ^{silicon} wafer to form desired patterns to partially expose the one surface of said ^{silicon} wafer through said patterns;

B removing said pad oxide film and said oxidation inhibitor film on said pad oxide film formed on the other surface of said ^{silicon} wafer to expose the whole area of the other surface of said ^{silicon} wafer;

B oxidizing the regions exposed partially on the one surface of said ^{silicon} wafer and the whole area of the other surface of said ^{silicon} wafer simultaneously to grow a silicon dioxide film on both surfaces of said ^{silicon} wafer; and

B removing said oxidation inhibitor film overlying said pad oxide film and the underlying pad oxide film remaining on the one surface of said silicon wafer;

B wherein said exposed regions on the one surface of said ^{silicon} wafer and the exposed whole area on the other surface of said silicon wafer are subjected to said oxidation process by a batch type thermal oxidation furnace.

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2. (original): A selective oxidation method according to Claim 1, wherein said oxidation inhibitor film is a silicon nitride film.
3. (currently amended): A selective oxidation method according to Claim 1, wherein said pad oxide films covering both surfaces of said silicon wafer are formed simultaneously in a batch type thermal oxidation furnace.
4. (currently amended): A selective oxidation method according to Claim 2, wherein said silicon nitride films covering both surfaces of said silicon wafer with interposition of said pad oxide film are formed simultaneously by a batch type low-pressure CVD.
5. (canceled)
6. (currently amended): A selective oxidation method according to Claim 1, wherein said oxide film partially formed on the one surface of said silicon wafer is used isolation regions.
7. (currently amended): A selective oxidation method according to Claim 1, wherein said oxide film formed on the whole area of the other surface of said silicon wafer is used as a sacrifice layer to remove contamination, which occurs in handling of said wafer, by an etching process.

B |
silicon